TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (Ultra-High-Speed U-MOSIII)

TPCA8020-H

High-Efficiency DC / DC Converter Applications Notebook PC Applications Portable Equipment Applications CCFL Inverter Applications

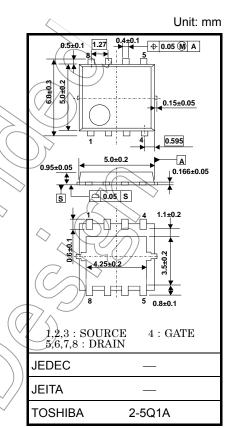
- Small footprint due to a small and thin package
- High speed switching
- Small gate charge: Q_{SW} = 3.5 nC (typ.)

Low drain-source ON-resistance: RDS (ON) = 22 m Ω (typ.)

- High forward transfer admittance: $|Y_{fs}| = 15 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- Enhancement mode: $V_{th} = 1.1$ to 2.3 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

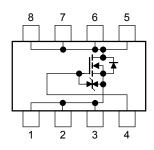
Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	 ✓ Unit
Drain-source voltage			V _{DSS}	40	V
Drain-gate voltage (R_{GS} = 20 k Ω)			V _{DGR} <	40	X
Gate-source voltage			VGSS	±20	$\langle \mathbf{x} \rangle$
Drain current	DC	(Note 1)	ID	7.5	A
Drain current	Pulse	(Note 1)		30	
Drain power dissipation (Tc= 25° C)				30 —	W
Drain power dissipation (t = 10 s) (Note 2a)			PD	2.8	A
Drain power dissipation (t = 10 s) (Note 2b)			PD	1.6	W
Single-pulse avalanche energy (Note 3)			EAS	26	mJ
Avalanche current		I _{AR}	7.5	А	
Repetitive avalanche energy Single-device value/ât dual operation (Note 2a, 4)			EAR	1.9	mJ
Channel temperature			Tch	150	°C
Storage temperature range			Tstg	-55 to 150	°C



Weight: 0.066 g (typ.)

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

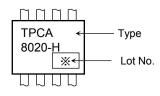
This transistor is an electrostatic-sensitive device. Handle with care.

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Thermal Characteristics

Characteristic	Symbol	Max	Unit	
Thermal resistance, channel to case $(\mbox{Tc=}25^\circ\ \ \mbox{C})$	R _{th (ch-c)}	4.17	°C/W	
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W	

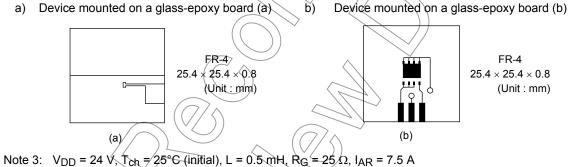
Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2:

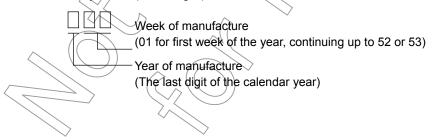
a) Device mounted on a glass-epoxy board (a)



b)

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



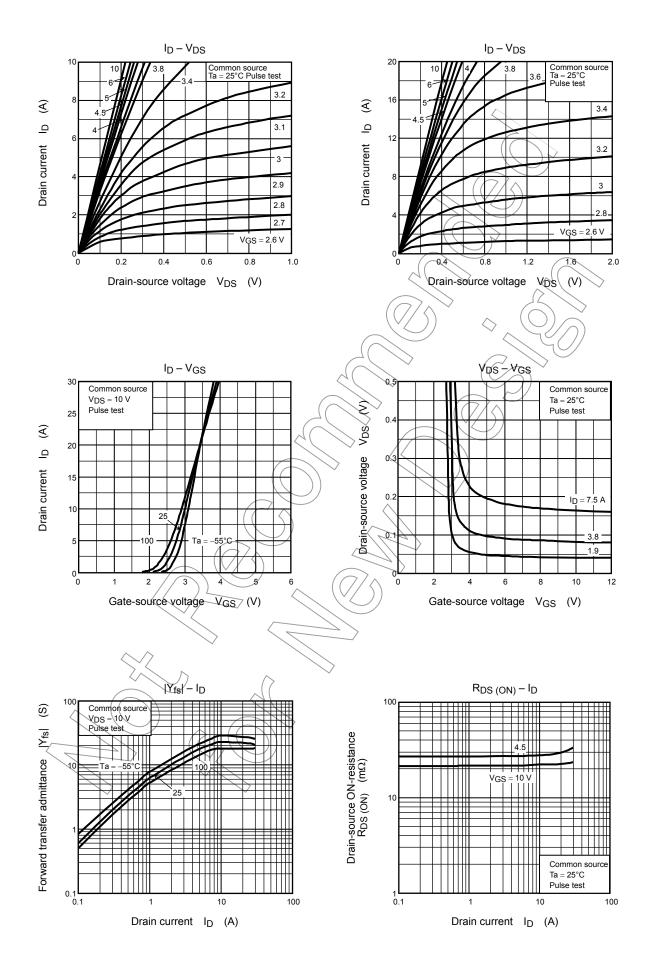
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_		±10	μA
Drain cutoff curr	rent	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	_		10	μA
Drain-source breakdown voltage		V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V		_	_	V
		V (BR) DSX	I _D = 10 mA, V _{GS} = -20 V	25		_	v
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	(h)	-7(2.3	V
Drain-source ON-resistance		R _{DS (ON)}	V _{GS} = 4.5 V, I _D = 3.8 A		27	35	mΩ
		R _{DS (ON)}	V _{GS} = 10 V, I _D = 3.8 A	\mathcal{A}	22	27	1115.2
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 3.8 A	7.5	15	_	S
Input capacitance		C _{iss}			650		
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		55	1	pF
Output capacitance		C _{oss}			240	\searrow	
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0} V \qquad V_{D} = 3.8 A$		3	> _	• ns
	Turn-on time	t _{on}			9		
	Fall time	tf		\mathbb{R}	2		
	Turn-off time	t _{off}	$Puty \leq 1\%, t_W = 10 \ \mu s$) _	18	—	
Total gate charge		Qg ($V_{DD} = 32 V$, $V_{GS} = 10 V$, $I_{D} = 7.5 A$		11		
(gate-source plus gate-drain)			$V_{DD} = 32 V, V_{GS} = 5 V, I_D = 7.5 A$	_	6.2	_	
Gate-source charge		Qgs			2.1		nC
Gate-drain ("Miller") charge		Qgd	$V_{DD} \simeq 32 V$, $V_{GS} = 10 V$, $I_D = 7.5 A$	_	2.7	_	
Gate switching charge		Qsw		_	3.5	_	

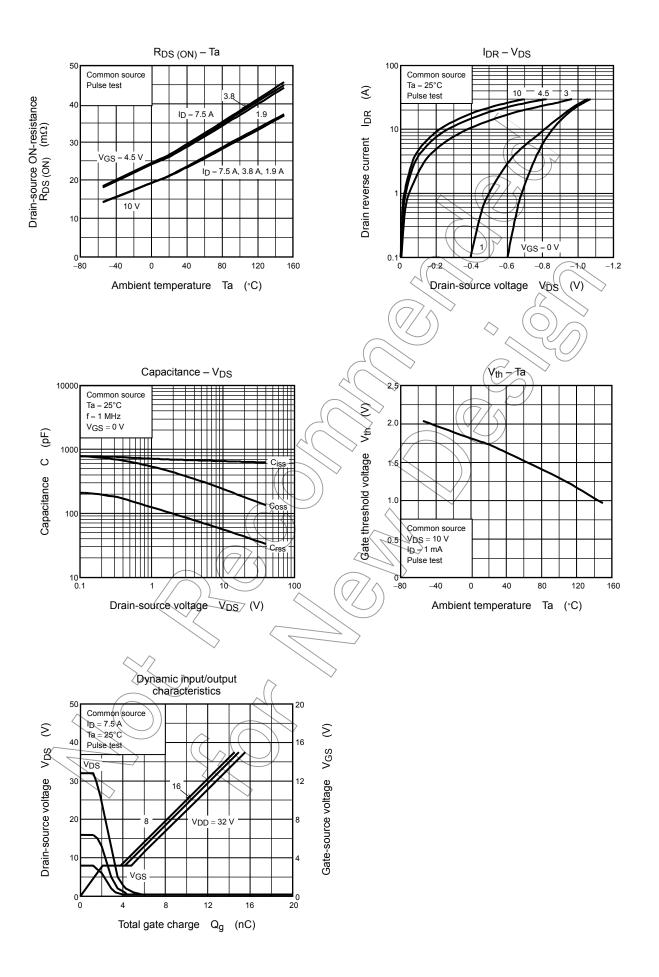
Source-Drain Ratings and Characteristics ($Ta = 25^{\circ}C$)

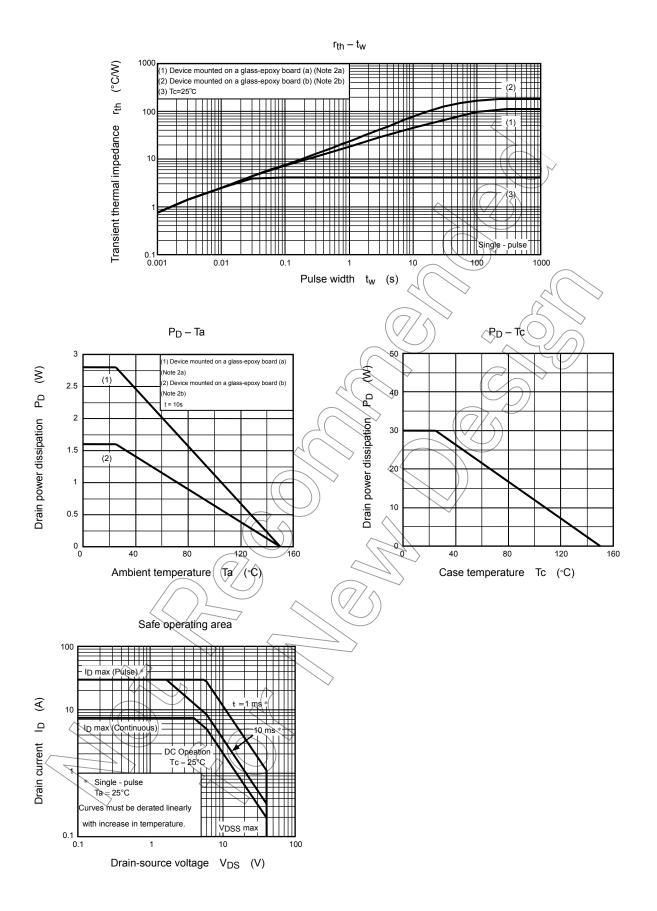
Characteristic	> Symbol $<$	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)		-	_		30	А
Forward voltage (diode)	VDSF	I _{DR} = 7.5 A, V _{GS} = 0 V			-1.2	V

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